

AC/DC Drivers

PWM type DC/DC converter IC Included 650V MOSFET

BM2Pxx2 Series

General Description

The PWM type DC/DC converter for AC/DC provide an optimum system for all products that include an electrical outlet.

This IC supports both isolated and non-isolated devices, enabling simpler design of various types of low-power electrical converters.

This IC built in a HV starter circuit that tolerates 650V, it contributes to low-power consumption.

With current detection resistors as external devices, a higher degree of design freedom is achieved. Since current mode control is utilized, current is restricted in each cycle and excellent performance is demonstrated in bandwidth and transient response.

The switching frequency is 65 kHz. At light load, the switching frequency is reduced and high efficiency is achieved.

A frequency hopping function is also on chip, which contributes to low EMI.

We can design easily, because This IC includes the switching MOSFET.

Basic specifications

■ Operating Power Supply Voltage Range:

VCC 8.9V to 26.0V DRAIN: to 650V

■ Operating Current: Normal Mode

BM2P012: 0.950mA (Typ.)

BM2P032: 0.775mA (Typ.)

BM2P052: 0.600mA (Typ.)

BM2P092: 0.500mA (Typ.)

Burst Mode: 0.400mA(Typ.)

65kHz(Typ.)

■ Oscillation Frequency:

■ Operating Temperature:

- 40°C to +105°C

■ MOSFET ON Resistance:

BM2P012: 1.4Ω (Typ.)

BM2P032: 2.4Ω (Typ.)

BM2P052: 4.0Ω (Typ.)

BM2P092: 8.5Ω (Typ.)

Features

- PWM frequency : 65kHz
- PWM current mode method
- Burst operation when load is light
- Frequency reduction function
- Built-in 650V start circuit
- Built-in 650V switching MOSFET
- VCC pin under voltage protection
- VCC pin overvoltage protection
- SOURCE pin Open protection
- SOURCE pin Short protection
- SOURCE pin Leading-Edge-Blanking function
- Per-cycle over current protection circuit
- Soft start
- Secondary Over current protection circuit
- BR pin AC input low voltage protection
- BR pin AC input high voltage protection

Package

DIP7K

W(Typ.) x D(Typ.) x H(Max.)

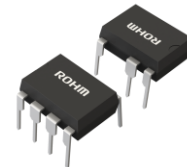
9.27mm x 6.35mm x 8.63mm

Pitch 2.54mm(Typ.)

DIP7F

9.20mm x 6.35mm x 7.60mm

Pitch 2.54mm(Typ.)



Applications

AC adapters and household appliances (vacuum cleaners, humidifiers, air cleaners, air conditioners, IH cooking heaters, rice cookers, etc.)

Line up

| Product | MOSFET ON resistor |
|---------|--------------------|
| BM2P012 | 1.4Ω |
| BM2P032 | 2.4Ω |
| BM2P052 | 4.0Ω |
| BM2P092 | 8.5Ω |

Application circuit

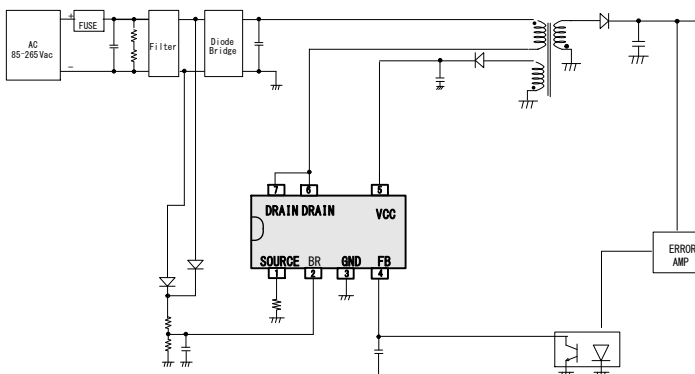


Figure 1. Application circuit

Absolute Maximum Ratings (Ta=25°C)

| Parameter | Symbol | Rating | Unit | Conditions |
|------------------------------|-------------------|-------------|------|---|
| Maximum applied voltage 1 | V _{max1} | -0.3 to 30 | V | VCC |
| Maximum applied voltage 2 | V _{max2} | -0.3 to 6.5 | V | SOURCE, FB, BR |
| Maximum applied voltage 3 | V _{max3} | 650 | V | DRAIN |
| Drain current pulse | I _{DP} | 10.40 | A | P _W =10us, Duty cycle=1% (BM2P012) |
| Drain current pulse | I _{DP} | 5.20 | A | P _W =10us, Duty cycle=1% (BM2P032) |
| Drain current pulse | I _{DP} | 2.60 | A | P _W =10us, Duty cycle=1% (BM2P052) |
| Drain current pulse | I _{DP} | 1.30 | A | P _W =10us, Duty cycle=1% (BM2P092) |
| Allowable dissipation | P _d | 2000 | mW | |
| Operating temperature range | T _{opr} | -40 to +105 | °C | |
| Maximum Junction Temperature | T _{JMAX} | 150 | °C | |
| Storage temperature range | T _{str} | -55 to +150 | °C | |

(Note1) When mounted (on 74.2 mm × 74.2 mm × 1.6 mm thick, glass epoxy on double-layer substrate).

Reduce to 16 mW/°C when Ta = 25°C or above.

Operating Conditions (Ta=25°C)

| Parameter | Symbol | Rating | Unit | Conditions |
|------------------------------|--------------------|-------------|------|-------------------|
| Power supply voltage range 1 | V _{CC} | 8.9 to 26.0 | V | VCC pin voltage |
| Power supply voltage range 2 | V _{DRAIN} | to 650 | V | DRAIN pin voltage |

Electrical Characteristics of MOSFET part (Unless otherwise noted, Ta = 25°C, VCC = 15 V)

| Electrical Characteristics of MOSFET part (Unless otherwise noted, $T_a = 25^{\circ}\text{C}$, $V_{GS} = 10\text{V}$) | | | | | | |
|---|---------------|----------------|-----|------|---------------|---|
| Parameter | Symbol | Specifications | | | Unit | Conditions |
| | | Min | Typ | Max | | |
| [MOSFET Block] | | | | | | |
| Between drain and source voltage | $V_{(BR)DDS}$ | 650 | - | - | V | $I_D=1\text{mA} / V_{GS}=0\text{V}$ |
| Drain leak current | I_{DSS} | - | - | 100 | μA | $V_{DS}=650\text{V} / V_{GS}=0\text{V}$ |
| On resistance | $R_{DS(ON)}$ | - | 1.4 | 2.0 | Ω | $I_D=0.25\text{A} / V_{GS}=10\text{V}$ (BM2P012) |
| On resistance | $R_{DS(ON)}$ | - | 2.4 | 3.6 | Ω | $I_D=0.25\text{A} / V_{GS}=10\text{V}$ (BM2P032) |
| On resistance | $R_{DS(ON)}$ | - | 4.0 | 5.5 | Ω | $I_D=0.25\text{A} / V_{GS}=10\text{V}$ (BM2P052) |
| On resistance | $R_{DS(ON)}$ | - | 8.5 | 12.0 | Ω | $I_D=0.25\text{A} / V_{GS}=10\text{V}$ (BM2P092) |

Electrical Characteristics of Control IC part (Unless otherwise noted, Ta = 25°C, VCC = 15 V)

| Parameter | Symbol | Specifications | | | Unit | Conditions |
|---|---------------------|----------------|-------------------------|-------|-------|---|
| | | Min | Typ | Max | | |
| [Circuit current] | | | | | | |
| Circuit current (ON) 1 | I _{ON1} | 700 | 950 | 1200 | μA | BM2P012 FB=2.0V (at pulse operation) |
| Circuit current (ON) 1 | I _{ON1} | 550 | 775 | 1050 | μA | BM2P032 FB=2.0V (at pulse operation) |
| Circuit current (ON) 1 | I _{ON1} | 410 | 600 | 790 | μA | BM2P052 FB=2.0V (at pulse operation) |
| Circuit current (ON) 1 | I _{ON1} | 350 | 500 | 650 | μA | BM2P092 FB=2.0V (at pulse operation) |
| Circuit current (ON) 2 | I _{ON2} | - | 400 | 500 | μA | FB=0.0V(at burst operation) |
| [VCC protection function] | | | | | | |
| VCC UVLO voltage 1 | V _{UVLO1} | 12.50 | 13.50 | 14.50 | V | VCC rises |
| VCC UVLO voltage 2 | V _{UVLO2} | 7.50 | 8.20 | 8.90 | V | VCC falls |
| VCC UVLO hysteresis | V _{UVLO3} | - | 5.30 | - | V | V _{UVLO3} = V _{UVLO1} - V _{UVLO2} |
| VCC OVP voltage 1 | V _{OVP1} | 26.0 | 27.5 | 29.0 | V | VCC rises |
| VCC OVP voltage 2 | V _{OVP2} | | 23.5 | | V | VCC falls |
| Latch released VCC voltage | V _{LATCH} | - | V _{UVLO2} -0.5 | - | V | |
| VCC Recharge start voltage | V _{CHG1} | 7.70 | 8.70 | 9.70 | V | |
| VCC Recharge stop voltage | V _{CHG2} | 12.00 | 13.00 | 14.00 | V | |
| Latch mask time | T _{LATCH} | 50 | 100 | 150 | us | |
| Thermal shut down temperature | T _{SD} | 118 | 145 | - | °C | Control IC |
| [PWM type DCDC driver block] | | | | | | |
| Oscillation frequency 1 | F _{SW1} | 60 | 65 | 70 | KHz | FB=2.00V |
| Oscillation frequency 2 | F _{SW2} | 20 | 25 | 30 | KHz | FB=0.40V |
| Frequency hopping width 1 | F _{DEL1} | - | 4.0 | - | KHz | FB=2.0V |
| Hopping fluctuation frequency | F _{CH} | 75 | 125 | 175 | Hz | |
| Soft start time 1 | T _{SS1} | 0.30 | 0.50 | 0.70 | ms | |
| Soft start time 2 | T _{SS2} | 0.60 | 1.00 | 1.40 | ms | |
| Soft start time 3 | T _{SS3} | 1.20 | 2.00 | 2.80 | ms | |
| Soft start time 4 | T _{SS4} | 4.80 | 8.00 | 11.20 | ms | |
| Maximum duty | D _{max} | 68.0 | 75.0 | 82.0 | % | |
| FB pin pull-up resistance | R _{FB} | 23 | 30 | 37 | kΩ | |
| ΔFB / ΔCS gain | Gain | - | 4.00 | - | V/V | |
| FB burst voltage | V _{BST} | 0.300 | 0.400 | 0.500 | V | FB falls |
| FB voltage of starting Frequency reduction mode | V _{DLT} | 1.100 | 1.250 | 1.400 | V | |
| FB OLP voltage 1a | V _{FOLP1A} | 2.60 | 2.80 | 3.00 | V | Overload is detected (FB rise) |
| FB OLP voltage 1b | V _{FOLP1B} | - | 2.60 | - | V | Overload is detected (FB drop) |
| FB OLP ON timer | T _{FOLP1} | 40 | 64 | 88 | ms | |
| FB OLP Start up timer | T _{FOLP1b} | 26 | 32 | 38 | ms | |
| FB OLP OFF timer | T _{FOLP2} | 358 | 512 | 666 | ms | |
| [Over current detection block] | | | | | | |
| Overcurrent detection voltage | V _{CS} | 0.380 | 0.400 | 0.420 | V | Ton=0us |
| Overcurrent detection voltage SS1 | V _{CS_SS1} | - | 0.100 | - | V | 0[ms] ~ Tss1[ms] |
| Overcurrent detection voltage SS2 | V _{CS_SS2} | - | 0.150 | - | V | Tss1 [ms] ~ Tss2 [ms] |
| Overcurrent detection voltage SS3 | V _{CS_SS3} | - | 0.200 | - | V | Tss2 [ms] ~ Tss3[ms] |
| Overcurrent detection voltage SS4 | V _{CS_SS4} | - | 0.300 | - | V | Tss3 [ms] ~ Tss4 [ms] |
| Leading Edge Blanking Time | T _{LEB} | - | 250 | - | ns | |
| Over current detection AC Voltage compensation factor | K _{CS} | 12 | 20 | 28 | mV/us | |
| SOURCE pin short protection voltage | V _{CSSHT} | 0.020 | 0.050 | 0.080 | V | |
| [Start circuit block] | | | | | | |
| Start current 1 | I _{START1} | 0.100 | 0.500 | 1.000 | mA | VCC= 0V |
| Start current 2 | I _{START2} | 1.000 | 3.000 | 6.000 | mA | VCC=10V |
| OFF current | I _{START3} | - | 10 | 20 | uA | Inflow current from Drain pin after UVLO released UVLO. When MOSFET is OFF |
| Start current switching voltage | V _{SC} | 0.800 | 1.500 | 2.100 | V | |

Electrical Characteristics of Control IC part (Unless otherwise noted, Ta = 25°C, VCC = 15 V)

| Parameter | Symbol | Specifications | | | Unit | Conditions |
|-------------------------------|------------------|----------------|------|------|------|--|
| | | Min | Typ | Max | | |
| [BR pin function] | | | | | | |
| BR UVLO detection voltage1 | V _{BR1} | 0.45 | 0.50 | 0.55 | V | BR rises |
| BR UVLO detection voltage 2 | V _{BR2} | 0.29 | 0.35 | 0.41 | V | BR falls |
| BR UVLO hysteresis | V _{BR3} | - | 0.15 | - | V | V _{BR3} =V _{BR1} -V _{BR2} |
| BR UVLO detection delay time1 | T _{BR1} | 50 | 100 | 150 | us | BR rises |
| BR UVLO detection delay time2 | T _{BR2} | 150 | 256 | 350 | ms | BR falls |
| BR OVP detection voltage1 | V _{BR4} | 2.00 | 2.10 | 2.20 | V | BR rises |
| BR OVP detection valtage2 | V _{BR5} | 1.90 | 2.00 | 2.10 | V | BR falls |
| BR OVP hysteresis | V _{BR6} | - | 0.10 | - | V | V _{BR6} =V _{BR4} -V _{BR5} |
| BR OVP detection delay time1 | T _{BR3} | 50 | 100 | 150 | us | BR rises |
| BR OVP detection delay time2 | T _{BR4} | 50 | 100 | 150 | us | BR falls |

PIN DESCRIPTIONS

Table 1. Pin Description

| NO. | Pin Name | I/O | Function | ESD Diode | |
|-----|----------|-----|------------------------------|-----------|-----|
| | | | | VCC | GND |
| 1 | SOURCE | I/O | MOSFET SOURCE pin | ○ | ○ |
| 2 | BR | I | Input AC voltage monitor pin | - | ○ |
| 3 | GND | I/O | GND pin | ○ | - |
| 4 | FB | I | Feedback signal input pin | - | ○ |
| 5 | VCC | I | Power supply input pin | - | ○ |
| 6 | DRAIN | I/O | MOSFET DRAIN pin | - | - |
| 7 | DRAIN | I/O | MOSFET DRAIN pin | - | - |

I/O Equivalent Circuit Diagram

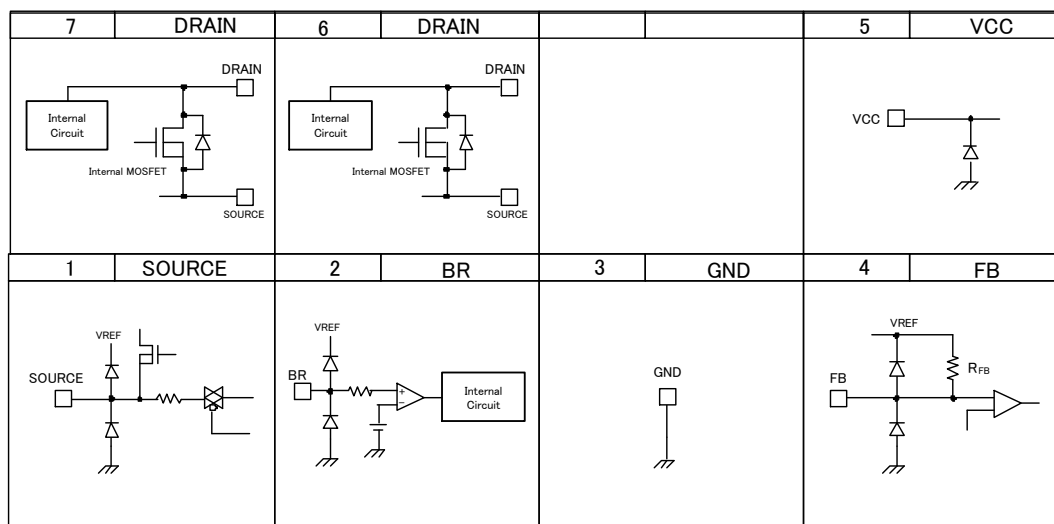


Figure 2. I/O Equivalent Circuit Diagram

Block Diagram

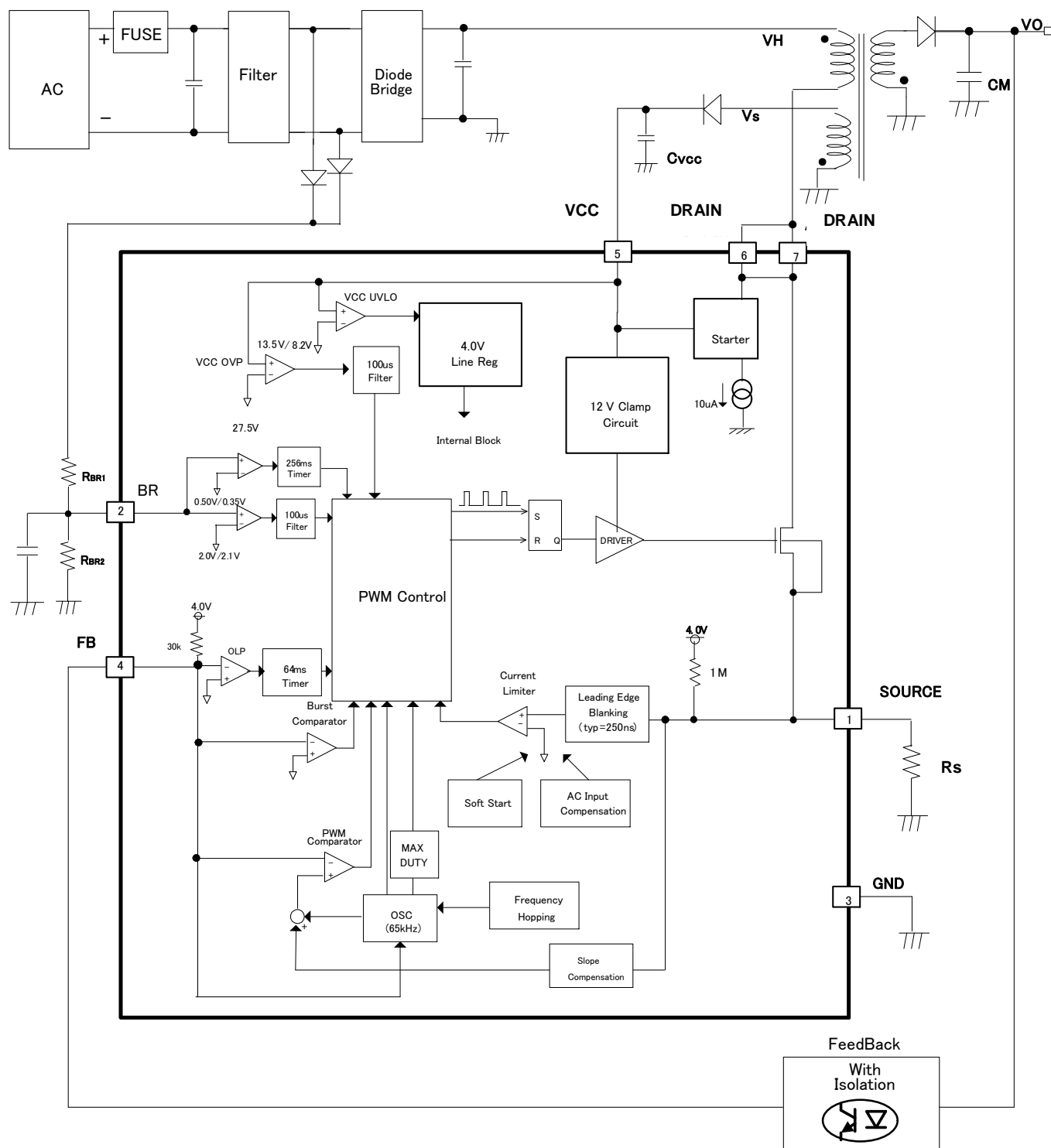


Figure 3. Block Diagram

Description of Blocks

(1) Start circuit (DRIAN: 6,7pin)

This IC built in Start circuit (tolerates 650V). It enables to be low standby mode electricity and high speed starting. After starting, consumption power is idling current I_{START3} (typ=10uA) only. Reference values of Starting time are shown in Figure-6. When $C_{VCC}=10\mu F$ it can start less than 0.1 sec.

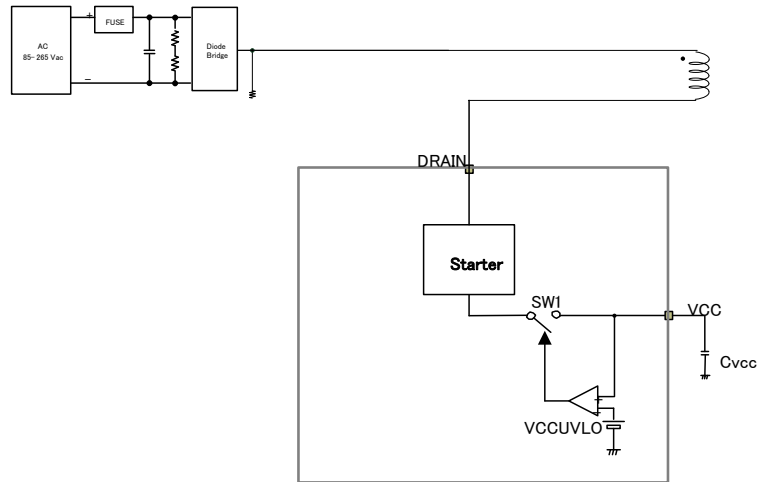


Figure 4. Block diagram of start circuit

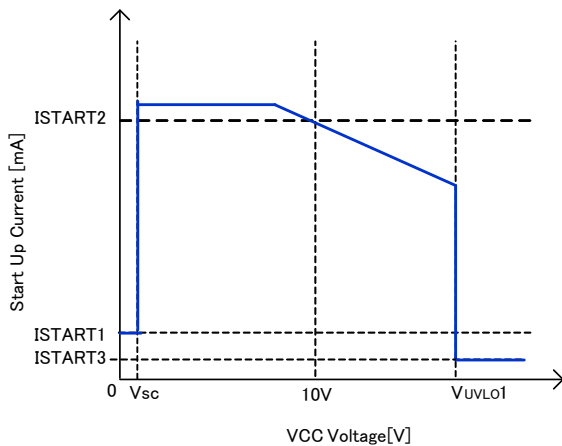


Figure 5. Start current vs VCC voltage

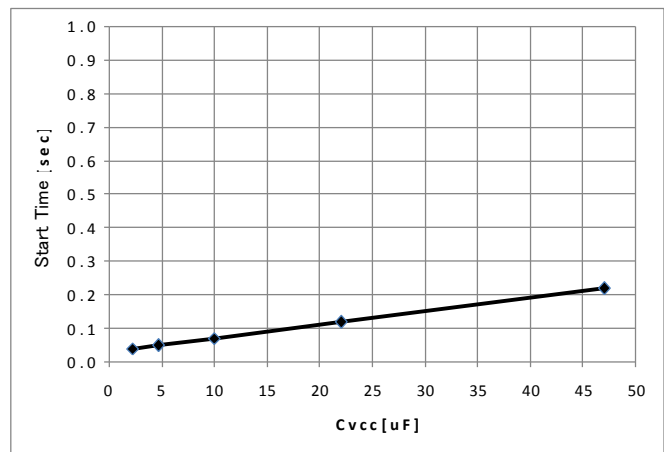


Figure 6. Start time (reference value)

* Start current flows from the DRAIN pin

Ex) Consumption power of start circuit only when the Vac=100V
 $P_{VH} = 100V \cdot \sqrt{2} \cdot 10\mu A = 1.41mW$

Ex) Consumption power of start circuit only when the Vac=240V
 $P_{VH} = 240V \cdot \sqrt{2} \cdot 10\mu A = 3.38mW$

(2) Start sequences

(Soft start operation, light load operation, and auto recovery operation during overload protection)
Start sequences are shown in Figure 7. See the sections below for detailed descriptions.

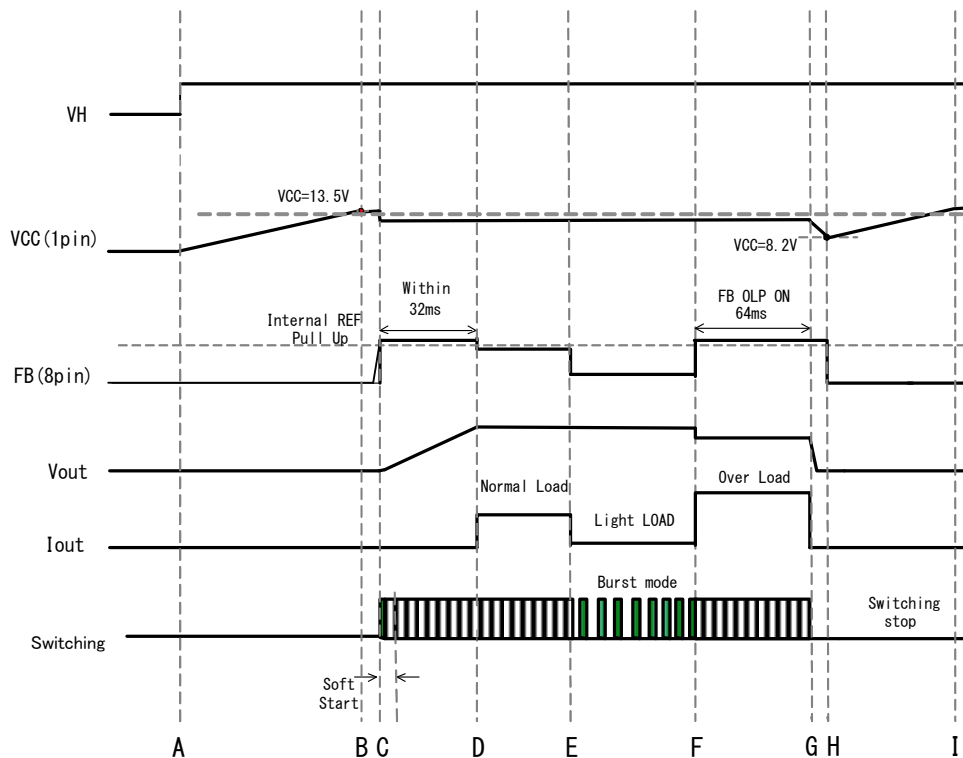


Figure 7. Start sequences Timing Chart

- A: Input voltage V_H is applied
- B: This IC starts operation when VCC pin voltage rises and $V_{CC} > V_{UVLO1}$ (13.5 V typ). Switching function starts when other protection functions are judged as normal. Until the secondary output voltage becomes constant level, VCC voltage drops because of the VCC consumption current. VCC recharge function start if VCC voltage $< V_{CHG1}$ (8.7V typ)
- C: With the soft start function, overcurrent limit value is restricted to prevent any excessive rise in voltage or current.
- D: When the switching operation starts, VOUT rises. The output voltage become to stable state, VCC voltage also become to stable state through auxiliary winding. Please set the rated voltage within the T_{FOLP1b} period (32ms typ) from VCC voltage $> V_{UVLO1}$.
- E: During a light load, if it reaches FB voltage $< V_{BST}$ ($= 0.4V_{typ}$), the IC starts burst operation to keep power consumption low. During burst operation, it becomes low-power consumption mode.
- F: When the FB Voltage $> V_{FOLP1A}$ ($= 2.8V_{typ}$), it becomes a overload operation.
- G: When FB pin voltage keeps V_{FOLP1A} ($= 2.8V_{typ}$) at or above T_{FOLP1} (64ms typ), the overload protection function is triggered and switching stops 64mS later. If the FB pin voltage becomes $FB < V_{FOLP1B}$ even once, the IC's FB OLP timer is reset.
- H: If the VCC voltage drops to $V_{CC} < V_{UVLO2}$ (8.2Vtyp) or below, restart is executed.
- I: The IC's circuit current is reduced and the VCC pin value rises. (Same as B)

(3) VCC pin protection function

This IC built in VCC low voltage protection function VCCUVLO (Under Voltage Lock Out), over voltage protection function VCC OVP (Over Voltage Protection) and VCC charge function that operates in case of dropping the VCC voltage.

VCC UVLO and VCC OVP monitor VCC pin and prevent VCC pin from destroying switching MOSFET at abnormal voltage.

VCC charge function stabilizes the secondary output voltage by charging from the high voltage line by start circuit at dropping the VCC voltage.

(3-1) VCC UVLO / VCC OVP function

VCCUVLO is auto recovery protection. VCCOVP is auto recovery protection. And they have voltage hysteresis. Refer to the operation figure-8.

Switching is stopped by the VCCOVP function when VCC pin voltage > V_{ovp1} (typ=27.5V), and Switching is restart when VCC pin voltage < V_{ovp2} (typ=23.5V)

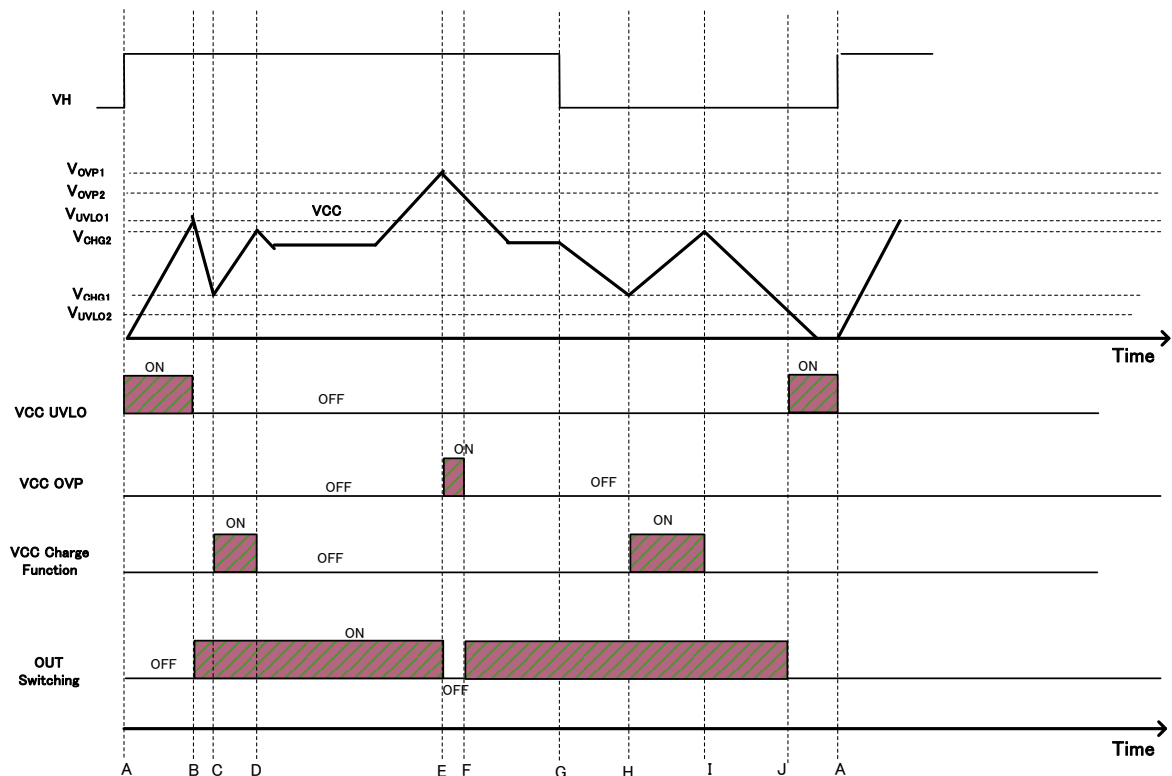


Figure 8. VCC UVLO / OVP Timing Chart

- A: DRAIN voltage input, VCC pin voltage starts rising.
- B: $V_{CC} > V_{UVLO1}$, DC/DC operation starts
- C: $V_{CC} < V_{CHG1}$, VCC charge function operates and the VCC voltage rises.
- D: $V_{CC} > V_{CHG2}$, VCC charge function is stopped.
- E: $V_{CC} > V_{OVP1}$, continues T_{LATCH} (typ =100us), switching is stopped by the VCCOVP function.
- F: $V_{CC} < V_{OVP2}$, Switching operation restarts
- G: VH is OPEN. VCC Voltage is fall.
- H: Same as C.
- I: Same as D.
- J: $V_{CC} < V_{UVLO2}$, Switching is stopped by the VCC UVLO function

(3-2) VCC Charge function

After VCC charge function operates once the VCC pin $>V_{UVLO1}$ and the DC/DC operation starts then the VCC pin voltage drops to $<V_{CHG1}$. At that time the VCC pin is charged from DRAIN pin through start circuit. By this operation, This IC doesn't occur to start failure.

When VCC pin voltage rises to $VCC > V_{CHG2}$, charge is stopped. The operations are shown in figure 9.

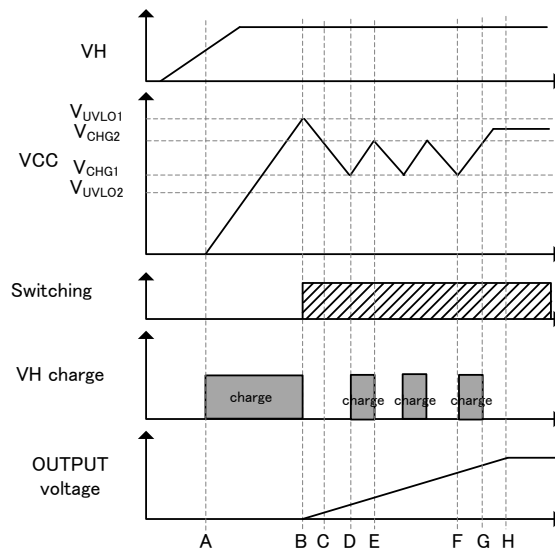


Figure 9. Charge operation VCC pin charge operation

- A: DRAIN pin voltage rises, charge starts to VCC pin by the VCC charge function.
- B: $VCC > V_{UVLO1}$, VCC UVLO function releases, VCC charge function stops, DC/DC operation starts.
- C: When DC/DC operation starts, the VCC voltage drops.
- D: $VCC < V_{CHG1}$, VCC recharge function operates and VCC pin voltage rises.
- E: $VCC > V_{CHG2}$, VCC recharge function stops.
- F: $VCC < V_{CHG1}$, VCC recharge function operates and VCC pin voltage rises.
- G: $VCC > V_{CHG2}$, VCC recharge function stops.
- H: After start of output voltage finished, VCC is charged by the auxiliary winding VCC pin stabilizes.

(4) DCDC driver (PWM comparator, frequency hopping, slope compensation, OSC, burst)

This IC is current mode PWM control.

An internal oscillator sets a fixed switching frequency (65 kHz typ).

This IC is integrated switching frequency hopping function which changes the switching frequency to fluctuate as shown in figure-10 below.

The fluctuation cycle is 125 Hz typ.

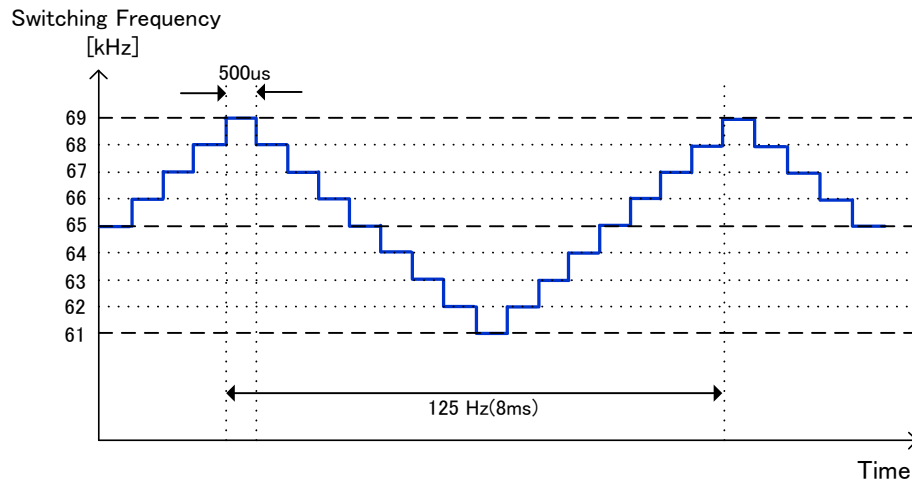


Figure 10. Frequency hopping function

Max duty cycle is fixed as 75% (typ) and MIN pulse width is fixed as 400 ns (typ).

With current mode control, when the duty cycle exceeds 50% sub harmonic oscillation may occur.

As a countermeasure to this, This IC is built in slope compensation circuits.

This IC is built in burst mode circuit and frequency reduction circuit to achieve lower power consumption, when the load is light.

FB pin is pull up by R_{FB} (30 kΩ typ).

FB pin voltage is changed by secondary output voltage (secondary load power).

FB pin is monitored, burst mode operation and frequency detection start.

Figure 11 shows the FB voltage, and switching frequency, DCDC operation

mode1 : Burst operation

mode2 : Frequency reduction operation.

mode3 : Fixed frequency operation. (operate at the max frequency)

mode4 : Over load operation. (detect the over load state and stop the pulse operation)

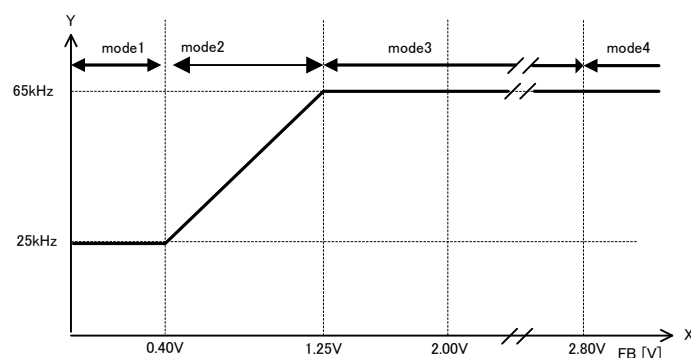


Figure 11. Switching operation state changes by FB pin voltage

(5) Over Current limiter

This IC is built in Over Current limiter per cycle. If the SOURCE pin exceeds a certain voltage, switching is stopped. It is also built in AC voltage compensation function. This is the function which compensates the maximum power as the AC voltage's change by increasing over current limiter with time.

Shown in figure-12, 13, and 14.

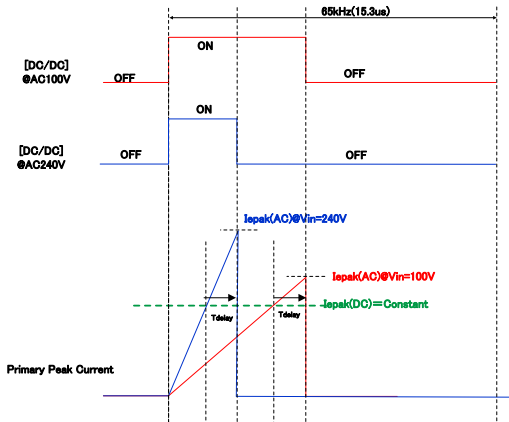


Figure 12. No AC voltage compensation function

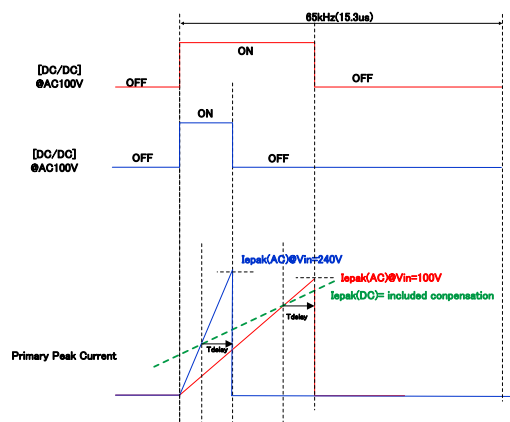


Figure13. Built-in AC compensation voltage

Primary peak current is decided as the formula below.

Primary peak current: $I_{peak} = V_{cs}/R_s + V_{dc}/L_p \cdot T_{delay}$

V_{cs} : Over current limiter voltage internal IC, R_s : Current detection resistance, V_{dc} : input DC voltage, L_p : Primary inductance,

T_{delay} : delay time after detection of over current limiter

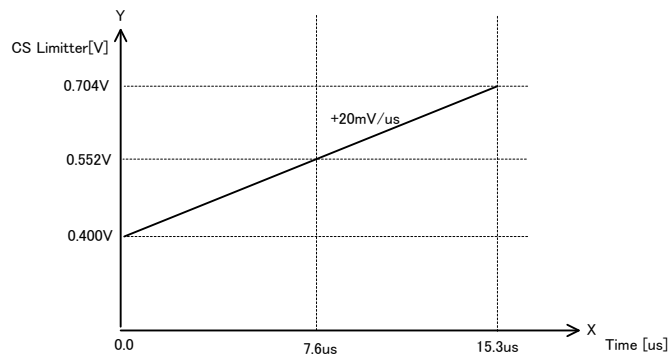


Figure 14. Over current limiter voltage

(6) L.E.B period

When the driver MOSFET is turned ON, surge current occurs at each capacitor component and drive current.

Therefore, because SOURCE pin voltage rises temporarily, the detection errors may occur in the over current limiter circuit.

To prevent detection errors, DRAIN is switched from high to low and the SOURCE signal is masked for 250 ns by the on-chip LEB (Leading Edge Blanking) function.

(7) SOURCE pin (1pin) short protection function

When the SOURCE pin (1pin) is shorted, This IC is over heat.
This IC built in short protection function to prevent destroying.

(8) SOURCE pin (1pin) open protection

If the SOURCE pin becomes OPEN, This IC may be damaged.
To prevent to be damaged, This IC built in OPEN protection circuit (auto recovery protection).

(9) Output over load protection function (FB OLP Comparator)

The output overload protection function monitors the secondary output load status at the FB pin, and stops switching when an overload occurs. In case of overload, the output voltage is reduced and current no longer flows to the photo coupler, so the FB pin voltage rises.

When the FB pin voltage $> V_{FOLP1A}$ (2.8 V typ) continuously for the period T_{FOLP1} (64ms typ), it is judged as an overload and stops switching.

When the FB pin $> V_{FOLP1A}$ (2.8 V typ), if the voltage goes lower than V_{FOLP1B} (2.6V typ) during the period T_{FOLP1} (64ms typ), the overload protection timer is reset. The switching operation is performed during this period T_{FOLP1} (64ms typ).

At startup, the FB voltage is pulled up to the IC's internal voltage, so operation starts at a voltage of V_{FOLP1A} (2.8 V typ) or above. Therefore, at startup the FB voltage must be set to go to V_{FOLP1B} (2.6 Vtyp) or below during the period T_{FOLP1} (64ms typ), and the secondary output voltage's start time must be set within the period T_{FOLP1} (64ms typ) following startup of the IC.

Recovery from the once detection of FBOLP, after the period T_{FOLP2} (512 ms typ)

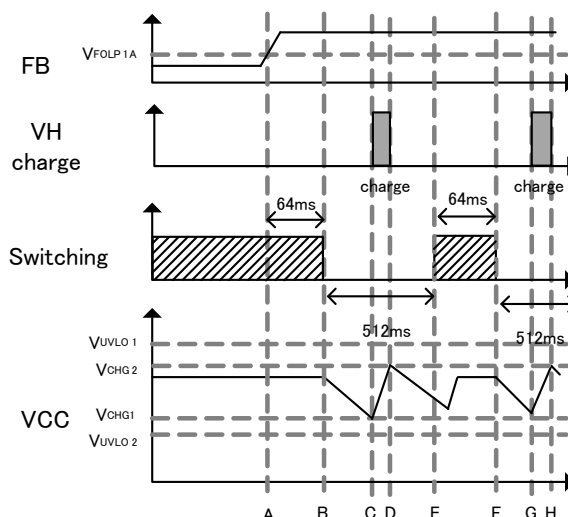


Figure 15. Over load protection (Auto recovery)

- A: The FBOLP comparator detects over load for $FB > V_{FOLP1A}$
- B: If the State of A continues for the period T_{FOLP1} (64ms typ), it is judged as an overload and stops switching after 64ms.
- C: While switching stops for the over load protection function, the VCC pin voltage drops and VCC pin voltage reaches $< V_{CHG1}$, the VCC charge function operates so the VCC pin voltage rises.
- D: VCC charge function stops when VCC pin voltage $> V_{CHG2}$
- E: If T_{FOLP2} (typ =512ms) go on from B point, Switching function starts on soft start.
- F: If T_{FOLP1} (typ=64ms) go on from E point to continues a overload condition ($FB > V_{FOLP1A}$), Switching function stops at F point.
- G: While switching stops VCC pin voltage drops to $< V_{CHG1}$, VCC charge function operates and VCC pin voltage rises.
- H: If VCC pin (5pin) voltage becomes over V_{CHG2} by the VCC charge function, VCC charge function operation stops.

(10) Input voltage protection function

This IC has BR-UVLO function and BR-OVP function to monitor input voltage. By monitoring input voltage, it can be prevented from breaking of IC. AC voltage and DC voltage can be monitored by BR pin.

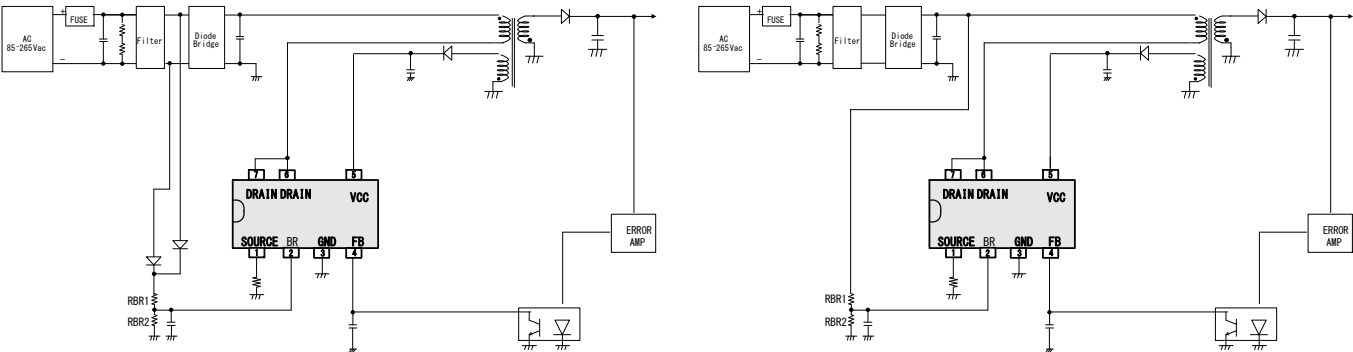


Figure 16(a). AC voltage monitor setting

Figure 16(b). DC voltage monitors setting

BRUVLO function can protect the breaking of IC when input voltage is low.

Operation mode of protection circuit

Operation mode of protection functions are shown in table2.

Table 2. Operation mode of protection circuit

| Function | Operation mode |
|------------------------------|----------------------------------|
| VCC Under Voltage Locked Out | Auto recovery |
| VCC Over Voltage Protection | Auto recovery |
| TSD | Latch (with 100us timer) |
| FB Over Limited Protection | Auto recovery (with 64ms timer) |
| SOURCE Open Protection | Auto recovery |
| BR UVLO | Auto recovery (with 256ms) |
| BR OVP | Auto recovery (with 100us timer) |

Sequence

The sequence diagram is show in Fig-17.
All condition transits OFF Mode $V_{CC} < 8.2V$

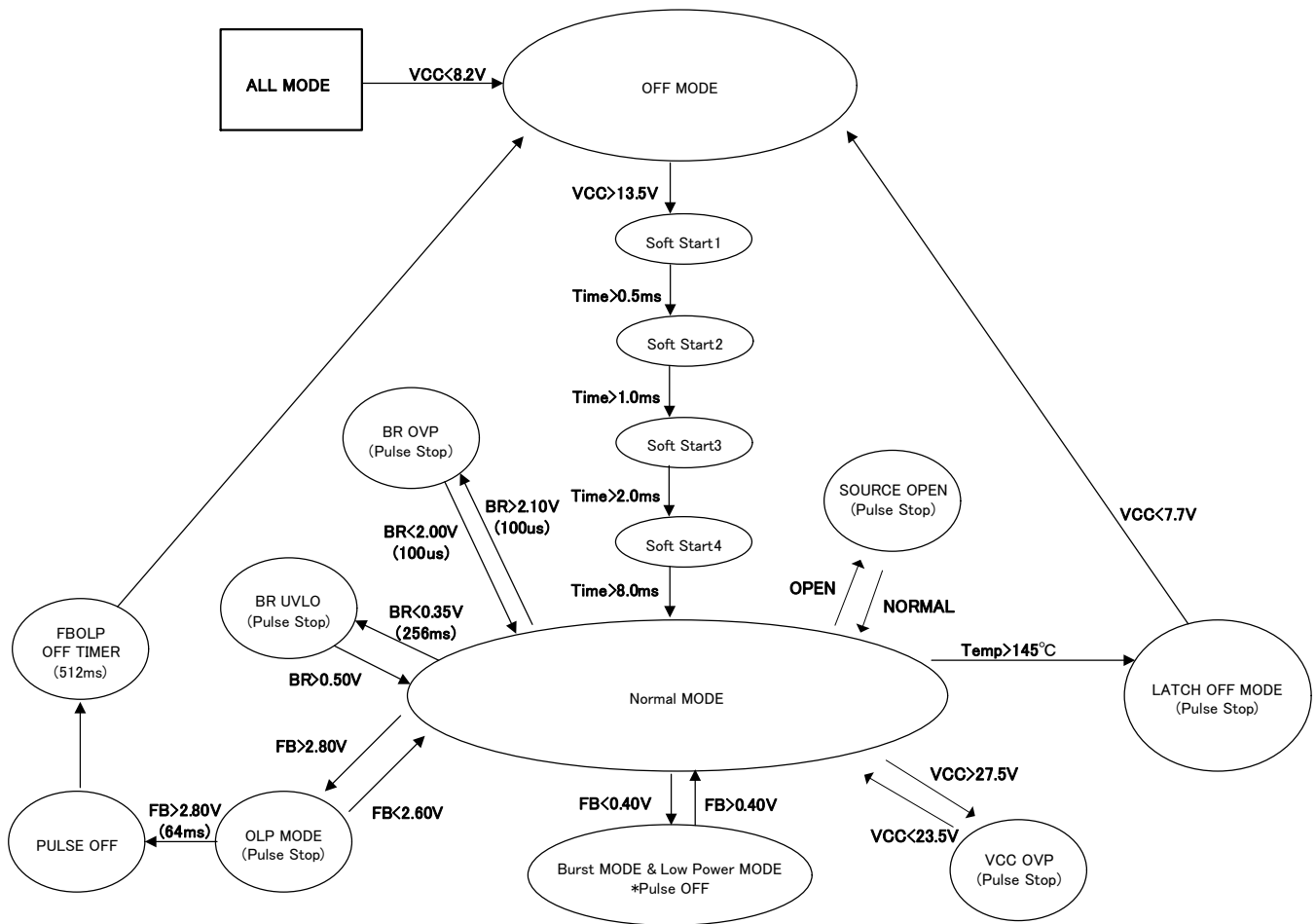


Figure 17. The sequence diagram

Thermal loss

The thermal design should set operation for the following conditions.
(Since the temperature shown below is the guaranteed temperature, be sure to take a margin into account.)

1. The ambient temperature T_a must be 105°C or less.
2. The IC's loss must be within the allowable dissipation P_d .

The thermal abatement characteristics are as follows.
(PCB: 74.2 mm × 74.2mm × 1.6 mm, mounted on glass epoxy double-layer substrate)

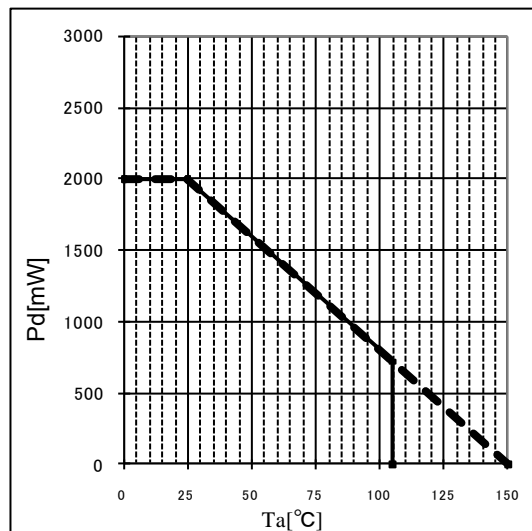
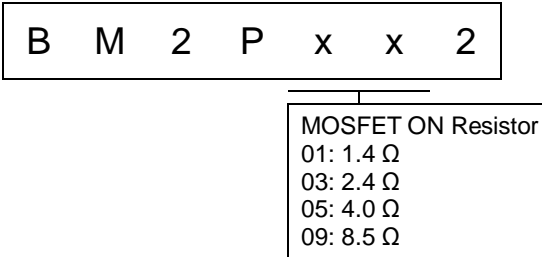
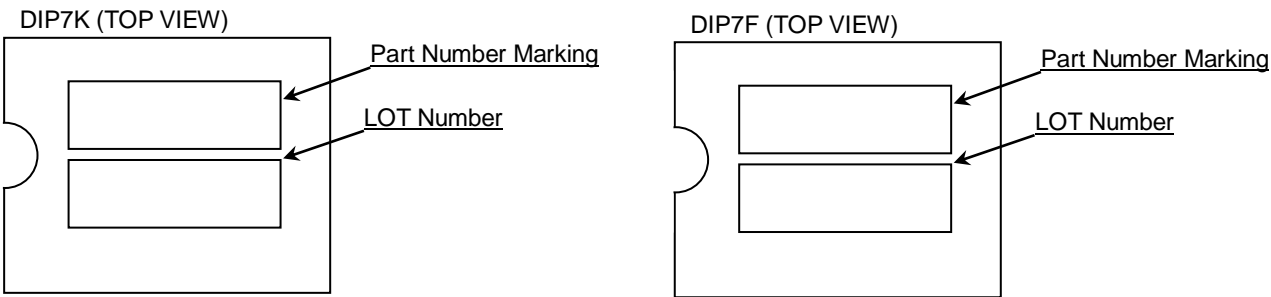


Figure 18. Thermal Abatement Characteristics

Ordering Information



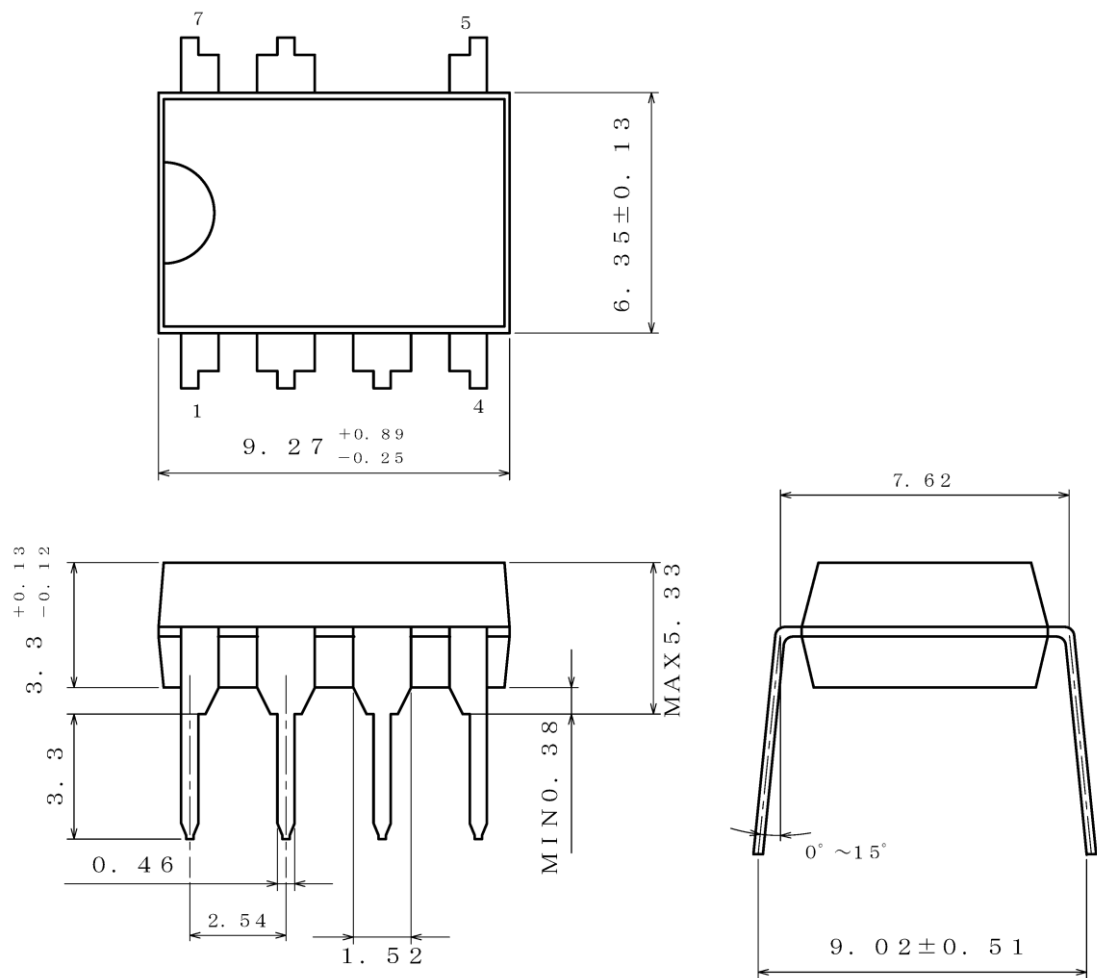
Making Diagram



| Part Number Marking | Product Name | MOSFET ON resistor |
|---------------------|--------------|--------------------|
| BM2P012 | BM2P012 | 1.4 Ω |
| BM2P032 | BM2P032 | 2.4 Ω |
| BM2P052 | BM2P052 | 4.0 Ω |
| BM2P092 | BM2P092 | 8.5 Ω |

Physical Dimension and Packing Information

| | |
|--------------|-------|
| Package Name | DIP7K |
|--------------|-------|



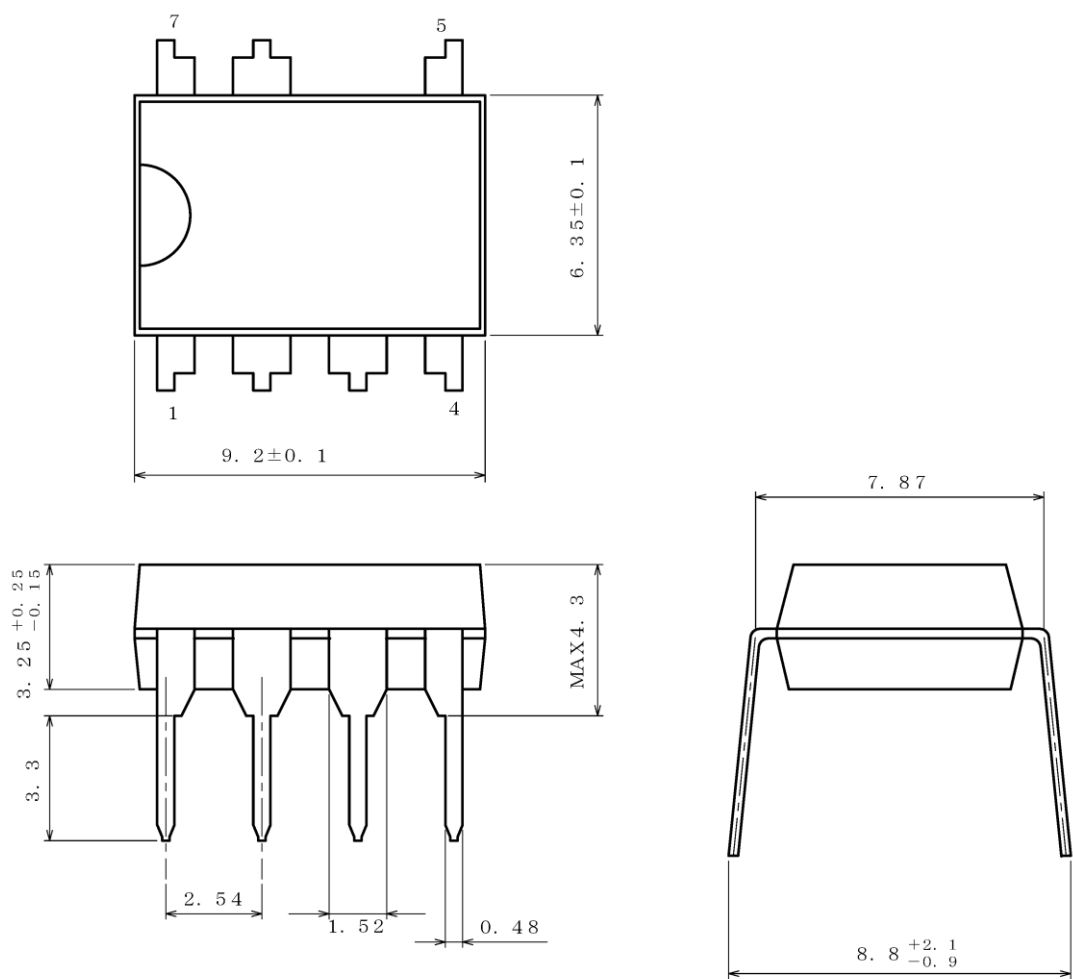
(UNIT : mm)
PKG : DIP7K
Drawing No. EX001-0076

< Container Information >

| | |
|-------------------|-------------------------------------|
| Container | Tube |
| Quantity | 2000pcs |
| Direction of feed | Packing orientation is same in tube |

Physical Dimension and Packing Information

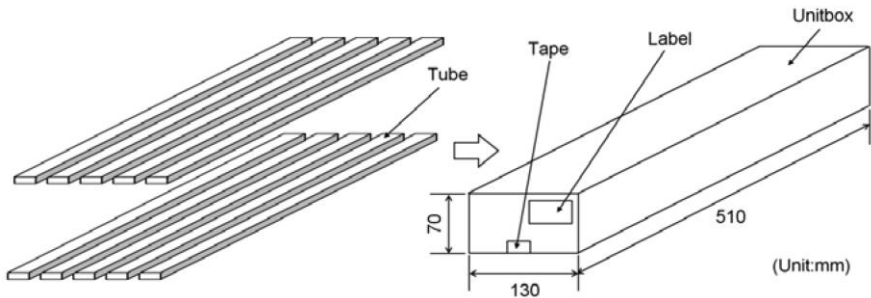
| | |
|--------------|-------|
| Package Name | DIP7F |
|--------------|-------|



(UNIT : mm)
PKG : DIP7F
Drawing No. EX001-0075

< Container Information >

| | |
|-------------------|--|
| Container | Tube |
| Quantity | 2000pcs |
| Direction of feed | Direction of products is fixed in a container tube |



Operational Notes

1. Reverse Connection of Power Supply

Connecting the power supply in reverse polarity can damage the IC. Take precautions against reverse polarity when connecting the power supply, such as mounting an external diode between the power supply and the IC's power supply pins.

2. Power Supply Lines

Design the PCB layout pattern to provide low impedance supply lines. Separate the GND and supply lines of the digital and analog blocks to prevent noise in the GND and supply lines of the digital block from affecting the analog block. Furthermore, connect a capacitor to GND at all power supply pins. Consider the effect of temperature and aging on the capacitance value when using electrolytic capacitors.

3. GND Voltage

Ensure that no pins are at a voltage below that of the GND pin at any time, even during transient condition.

4. GND Wiring Pattern

When using both small-signal and large-current GND traces, the two GND traces should be routed separately but connected to a single GND at the reference point of the application board to avoid fluctuations in the small-signal GND caused by large currents. Also ensure that the GND traces of external components do not cause variations on the GND voltage. The GND lines must be as short and thick as possible to reduce line impedance.

5. Thermal Consideration

Should by any chance the power dissipation rating be exceeded the rise in temperature of the chip may result in deterioration of the properties of the chip. The absolute maximum rating of the Pd stated in this specification is when the IC is mounted on a 70mm x 70mm x 1.6mm glass epoxy board. In case of exceeding this absolute maximum rating, increase the board size and copper area to prevent exceeding the Pd rating.

6. Recommended Operating Conditions

These conditions represent a range within which the expected characteristics of the IC can be approximately obtained. The electrical characteristics are guaranteed under the conditions of each parameter.

7. Inrush Current

When power is first supplied to the IC, it is possible that the internal logic may be unstable and inrush current may flow instantaneously due to the internal powering sequence and delays, especially if the IC has more than one power supply. Therefore, give special consideration to power coupling capacitance, power wiring, width of GND wiring, and routing of connections.

8. Operation Under Strong Electromagnetic Field

Operating the IC in the presence of a strong electromagnetic field may cause the IC to malfunction.

9. Testing on Application Boards

When testing the IC on an application board, connecting a capacitor directly to a low-impedance output pin may subject the IC to stress. Always discharge capacitors completely after each process or step. The IC's power supply should always be turned off completely before connecting or removing it from the test setup during the inspection process. To prevent damage from static discharge, GND the IC during assembly and use similar precautions during transport and storage.

10. Inter-pin Short and Mounting Errors

Ensure that the direction and position are correct when mounting the IC on the PCB. Incorrect mounting may result in damaging the IC. Avoid nearby pins being shorted to each other especially to GND, power supply and output pin. Inter-pin shorts could be due to many reasons such as metal particles, water droplets (in very humid environment) and unintentional solder bridge deposited in between pins during assembly to name a few.

Operational Notes – continued

11. Unused Input Pins

Input pins of an IC are often connected to the gate of a MOS transistor. The gate has extremely high impedance and extremely low capacitance. If left unconnected, the electric field from the outside can easily charge it. The small charge acquired in this way is enough to produce a significant effect on the conduction through the transistor and cause unexpected operation of the IC. So unless otherwise specified, unused input pins should be connected to the power supply or GND line.

12. Regarding the Input Pin of the IC

This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P-N junctions are formed at the intersection of the P layers with the N layers of other elements, creating a parasitic diode or transistor. For example (refer to figure below):

When $GND > Pin\ A$ and $GND > Pin\ B$, the P-N junction operates as a parasitic diode.

When $GND > Pin\ B$, the P-N junction operates as a parasitic transistor.

Parasitic diodes inevitably occur in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits, operational faults, or physical damage. Therefore, conditions that cause these diodes to operate, such as applying a voltage lower than the GND voltage to an input pin (and thus to the P substrate) should be avoided.

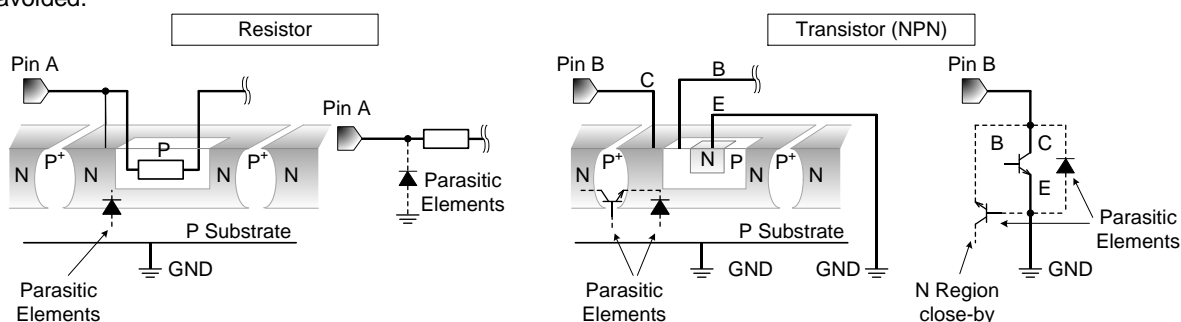


Figure 19. Example of monolithic IC structure

13. Ceramic Capacitor

When using a ceramic capacitor, determine the dielectric constant considering the change of capacitance with temperature and the decrease in nominal capacitance due to DC bias and others.

14. Area of Safe Operation (ASO)

Operate the IC such that the output voltage, output current, and power dissipation are all within the Area of Safe Operation (ASO).

15. Thermal Shutdown Circuit(TSD)

This IC has a built-in thermal shutdown circuit that prevents heat damage to the IC. Normal operation should always be within the IC's power dissipation rating. If however the rating is exceeded for a continued period, the junction temperature (T_j) will rise which will activate the TSD circuit that will turn OFF all output pins. The IC should be powered down and turned ON again to resume normal operation because the TSD circuit keeps the outputs at the OFF state even if the T_j falls below the TSD threshold.

Note that the TSD circuit operates in a situation that exceeds the absolute maximum ratings and therefore, under no circumstances, should the TSD circuit be used in a set design or for any purpose other than protecting the IC from heat damage.

16. Over Current Protection Circuit (OCP)

This IC incorporates an integrated overcurrent protection circuit that is activated when the load is shorted. This protection circuit is effective in preventing damage due to sudden and unexpected incidents. However, the IC should not be used in applications characterized by continuous operation or transitioning of the protection circuit.

Revision History

| date | Rev. No. | Revision Point |
|------------|----------|--|
| 2012.07.19 | 001 | New Release |
| 2013.11.18 | 003 | P7 An explanation for Figure7 P8 An explanation for VCC_UVLO/VCC_OVP function An explanation for Figure8 P11 An explanation for Over Current limiter P12 An explanation for Output over load protection function An explanation for Figure15 P13 Figure16 |
| 2015.05.15 | 004 | P14 Operation mode of protection circuit P14 Sequence |
| 2015.09.24 | 005 | P4 A value of BR UVLO detection voltage 1 P4 A value of BR UVLO voltage 2 P7 An explanation of Start sequence P8 An explanation of VCC pin protection function P8 An explanation of VCC UVLO / VCC OVP function P9 An explanation of VCC Charge function P11 An explanation of Over Current Limiter P12 An explanation of Output over load protection function |
| 2017.03.07 | 006 | P1 An explanation of package height P2 Format for Electrical Characteristics of MOSFET P3 Format for Electrical Characteristics of Control IC P3 An explanation of T hysteresis P4 An explanation of BR OVP hysteresis P5 An explanation of Figure3 P7 An explanation of Start sequences P8 An explanation of Figure8 P9 An explanation of VCC pin protection function P12 An explanation of OUTPUT over load protection function |
| 2019.04.22 | 007 | P1 Add the division of product name P1 Add the package variation and change the size P17, P18 Modify the physical dimension and packing information |

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| JAPAN | USA | EU | CHINA |
|-----------|-----------|------------|-----------|
| CLASS III | CLASS III | CLASS II b | CLASS III |
| CLASS IV | | CLASS III | |

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 - Use of the Products in places subject to dew condensation
- The Products are not subject to radiation-proof design.
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- In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse, is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
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- Confirm that operation temperature is within the specified range described in the product specification.
- ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

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